

# MOSFET - N-Channel Shielded Gate PowerTrench®

150 V, 10.9 mΩ, 74.3 A

## NTP011N15MC

### Features

- Shielded Gate MOSFET Technology
- Max  $R_{DS(on)} = 10.9 \text{ m}\Omega$  at  $V_{GS} = 10 \text{ V}$ ,  $I_D = 41 \text{ A}$
- 50% Lower  $Q_{rr}$  than other MOSFET Suppliers
- Lowers Switching Noise/EMI
- 100% UIL Tested
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Typical Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Motor Drives and Uninterruptible Power Supplies
- Micro Solar Inverter

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter                                                                                      |                                                |                       | Symbol                            | Value       | Unit |
|------------------------------------------------------------------------------------------------|------------------------------------------------|-----------------------|-----------------------------------|-------------|------|
| Drain-to-Source Voltage                                                                        |                                                |                       | V <sub>DSS</sub>                  | 150         | V    |
| Gate-to-Source Voltage                                                                         |                                                |                       | V <sub>GS</sub>                   | ±20         | V    |
| Continuous Drain Current R <sub>θJC</sub> (Note 2)                                             | Steady State                                   | T <sub>C</sub> = 25°C | I <sub>D</sub>                    | 74.3        | A    |
| Power Dissipation R <sub>θJC</sub> (Note 2)                                                    |                                                |                       | P <sub>D</sub>                    | 136.4       | W    |
| Continuous Drain Current R <sub>θJA</sub> (Notes 1, 2)                                         | Steady State                                   | T <sub>A</sub> = 25°C | I <sub>D</sub>                    | 9.8         | A    |
| Power Dissipation R <sub>θJA</sub> (Notes 1, 2)                                                |                                                |                       | P <sub>D</sub>                    | 2.4         | W    |
| Pulsed Drain Current                                                                           | T <sub>C</sub> = 25°C, t <sub>p</sub> = 100 μs |                       | I <sub>DM</sub>                   | 374         | A    |
| Operating Junction and Storage Temperature Range                                               |                                                |                       | T <sub>J</sub> , T <sub>stg</sub> | -55 to +175 | °C   |
| Single Pulse Drain-to-Source Avalanche Energy (I <sub>L</sub> = 14 A <sub>pk</sub> , L = 3 mH) |                                                |                       | E <sub>AS</sub>                   | 294         | mJ   |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s)                              |                                                |                       | T <sub>L</sub>                    | 260         | °C   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

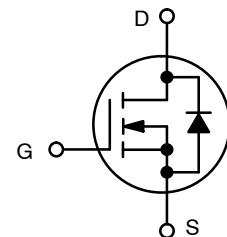
1. Surface-mounted on FR4 board using a 1 in<sup>2</sup>, 2 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.



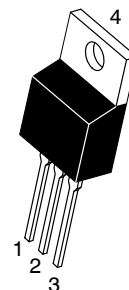
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| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|---------------|--------------------------|-------------------|
| 150 V         | 10.9 mΩ @ 10 V           | 74.3 A            |

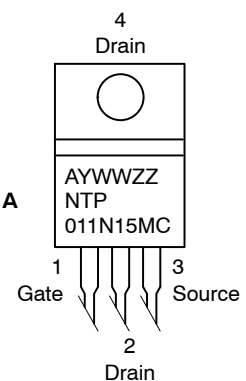


N-CHANNEL MOSFET



TO-220  
CASE 221A

### MARKING DIAGRAM



NTP011N15MC = Specific Device Code

A = Assembly Location

Y = Year

WW = Work Week

ZZ = Lot Traceability

### ORDERING INFORMATION

| Device      | Package             | Shipping†  |
|-------------|---------------------|------------|
| NTP011N15MC | TO-220<br>(Pb-Free) | 800 / Tube |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTP011N15MC

## THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter                                   | Symbol          | Value | Unit |
|---------------------------------------------|-----------------|-------|------|
| Junction-to-Case – Steady State (Note 2)    | $R_{\theta JC}$ | 1.1   | °C/W |
| Junction-to-Ambient – Steady State (Note 2) | $R_{\theta JA}$ | 62.5  |      |

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                           |                   |                                                            |     |    |           |               |
|-----------------------------------------------------------|-------------------|------------------------------------------------------------|-----|----|-----------|---------------|
| Drain-to-Source Breakdown Voltage                         | $V_{(BR)DSS}$     | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$        | 150 |    |           | V             |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ , ref to $25^\circ\text{C}$ |     | 83 |           | mV/°C         |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$         | $V_{GS} = 0\text{ V}, V_{DS} = 120\text{ V}$               |     |    | 1.0       | $\mu\text{A}$ |
| Gate-to-Source Leakage Current                            | $I_{GSS}$         | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$            |     |    | $\pm 100$ | nA            |

### ON CHARACTERISTICS

|                                            |                  |                                                            |     |      |      |            |
|--------------------------------------------|------------------|------------------------------------------------------------|-----|------|------|------------|
| Gate Threshold Voltage                     | $V_{GS(TH)}$     | $V_{GS} = V_{DS}, I_D = 223\text{ }\mu\text{A}$            | 2.5 |      | 4.5  | V          |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | $I_D = 223\text{ }\mu\text{A}$ , ref to $25^\circ\text{C}$ |     | -8.5 |      | mV/°C      |
| Drain-to-Source On Resistance              | $R_{DS(on)}$     | $V_{GS} = 10\text{ V}, I_D = 41\text{ A}$                  |     | 8.7  | 10.9 | m $\Omega$ |
|                                            |                  | $V_{GS} = 8\text{ V}, I_D = 20\text{ A}$                   |     | 9.3  | 12.6 |            |
| Forward Transconductance                   | $g_{FS}$         | $V_{DS} = 10\text{ V}, I_D = 41\text{ A}$                  |     | 85   |      | S          |

### CHARGES, CAPACITANCES & GATE RESISTANCE

|                              |              |                                                                 |  |      |     |          |
|------------------------------|--------------|-----------------------------------------------------------------|--|------|-----|----------|
| Input Capacitance            | $C_{ISS}$    | $V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 75\text{ V}$   |  | 2810 |     | pF       |
| Output Capacitance           | $C_{OSS}$    |                                                                 |  | 840  |     |          |
| Reverse Transfer Capacitance | $C_{RSS}$    |                                                                 |  | 14   |     |          |
| Gate-Resistance              | $R_G$        |                                                                 |  | 0.8  | 1.6 | $\Omega$ |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 75\text{ V}; I_D = 41\text{ A}$ |  | 37   |     | nC       |
| Threshold Gate Charge        | $Q_{G(TH)}$  |                                                                 |  | 9.1  |     |          |
| Gate-to-Source Charge        | $Q_{GS}$     |                                                                 |  | 15   |     |          |
| Gate-to-Drain Charge         | $Q_{GD}$     |                                                                 |  | 6.5  |     |          |
| Plateau Voltage              | $V_{GP}$     |                                                                 |  | 5.4  |     | V        |
| Output Charge                | $Q_{OSS}$    | $V_{DD} = 75\text{ V}, V_{GS} = 0\text{ V}$                     |  | 95   |     | nC       |

### SWITCHING CHARACTERISTICS (Note 3)

|                     |              |                                                                                          |  |     |  |    |
|---------------------|--------------|------------------------------------------------------------------------------------------|--|-----|--|----|
| Turn-On Delay Time  | $t_{d(ON)}$  | $V_{GS} = 10\text{ V}, V_{DD} = 75\text{ V}, I_D = 41\text{ A}, R_G = 4.7\text{ }\Omega$ |  | 19  |  | ns |
| Rise Time           | $t_r$        |                                                                                          |  | 14  |  |    |
| Turn-Off Delay Time | $t_{d(OFF)}$ |                                                                                          |  | 28  |  |    |
| Fall Time           | $t_f$        |                                                                                          |  | 5.1 |  |    |

### DRAIN-SOURCE DIODE CHARACTERISTICS

|                         |          |                                                                                                         |                          |     |      |     |    |
|-------------------------|----------|---------------------------------------------------------------------------------------------------------|--------------------------|-----|------|-----|----|
| Forward Diode Voltage   | $V_{SD}$ | $V_{GS} = 0\text{ V}, I_S = 41\text{ A}$                                                                | $T_J = 25^\circ\text{C}$ |     | 0.92 | 1.2 | V  |
| Reverse Recovery Time   | $t_{RR}$ | $V_{GS} = 0\text{ V}, V_{DD} = 75\text{ V}$<br>$di_S/dt = 300\text{ A}/\mu\text{s}, I_S = 41\text{ A}$  |                          | 49  |      |     | ns |
| Reverse Recovery Charge | $Q_{RR}$ |                                                                                                         |                          | 210 |      |     | nC |
| Reverse Recovery Time   | $t_{RR}$ | $V_{GS} = 0\text{ V}, V_{DD} = 75\text{ V}$<br>$di_S/dt = 1000\text{ A}/\mu\text{s}, I_S = 41\text{ A}$ |                          | 36  |      |     | ns |
| Reverse Recovery Charge | $Q_{RR}$ |                                                                                                         |                          | 421 |      |     | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

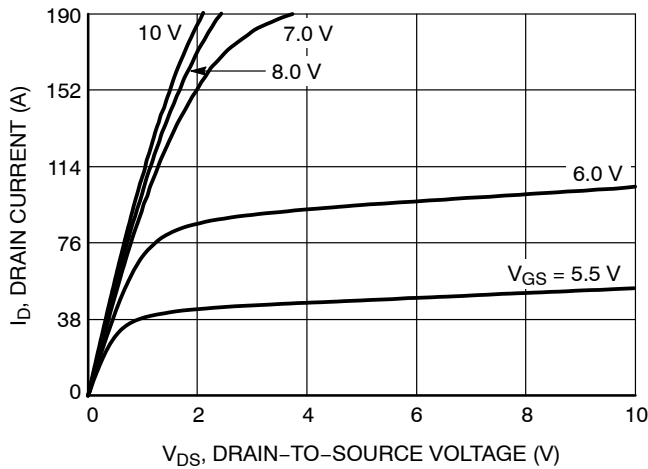


Figure 1. On-Region Characteristics

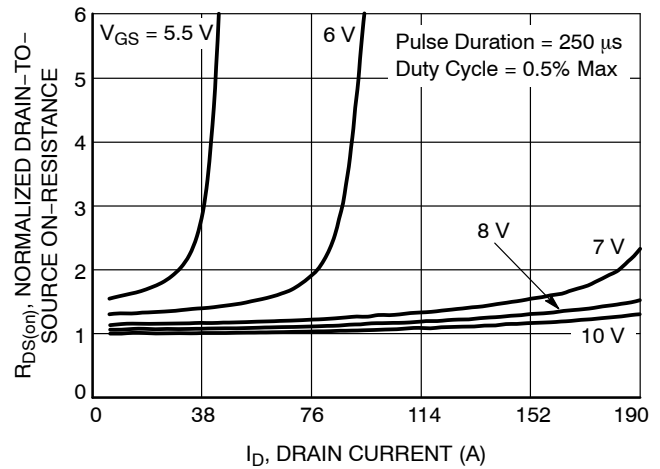


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

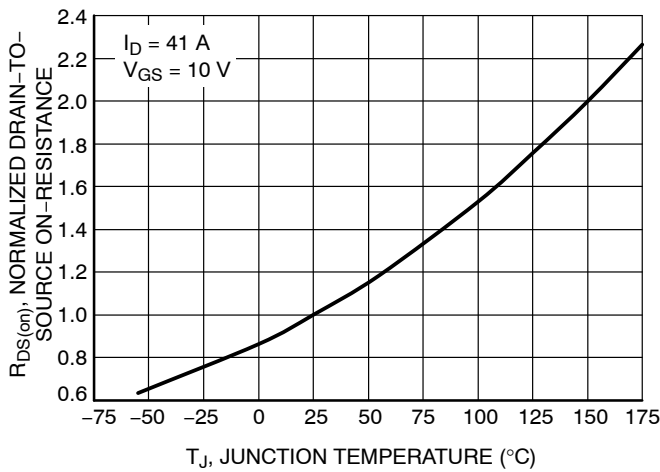


Figure 3. Normalized On-Resistance vs. Junction Temperature

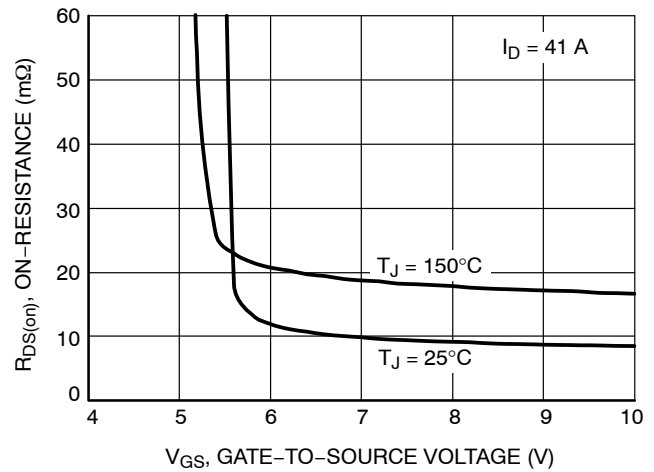


Figure 4. On-Resistance vs. Gate-to-Source Voltage

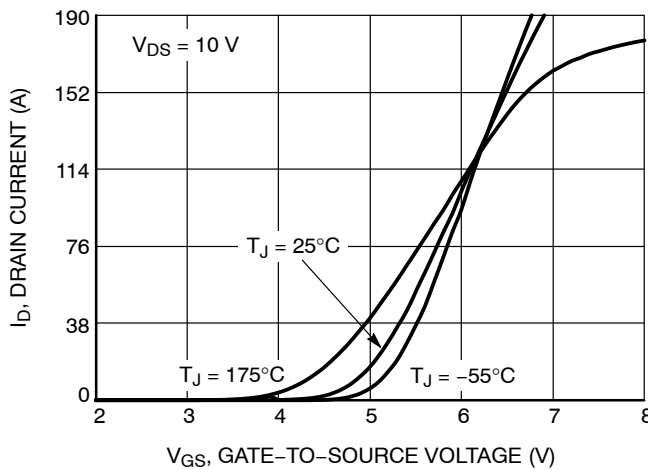


Figure 5. Transfer Characteristics

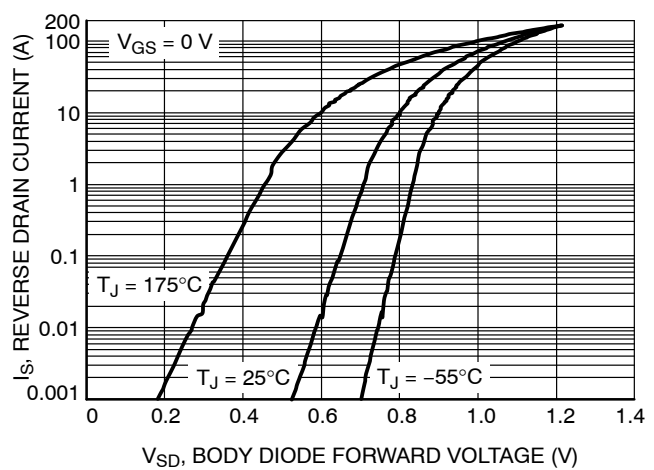


Figure 6. Source-to-Drain Diode Forward Voltage vs. Source Current

# TYPICAL CHARACTERISTICS

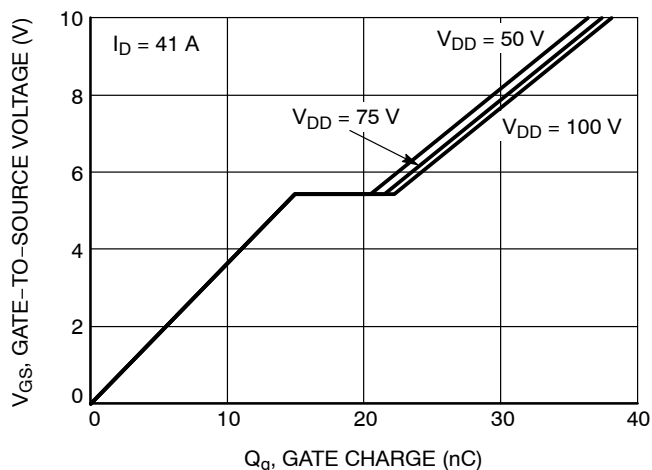


Figure 7. Gate Charge Characteristics

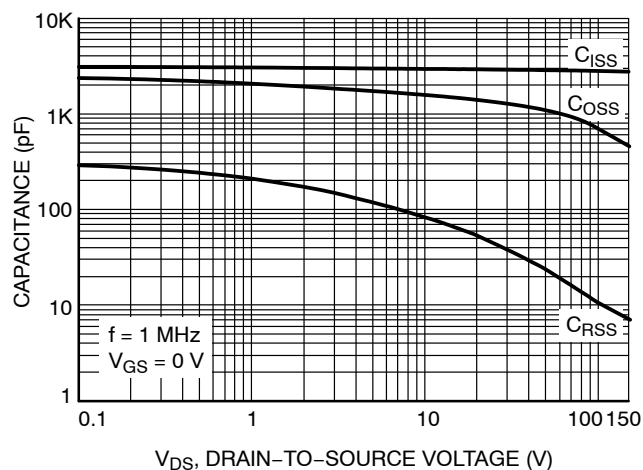


Figure 8. Capacitance vs. Drain-to-Source Voltage

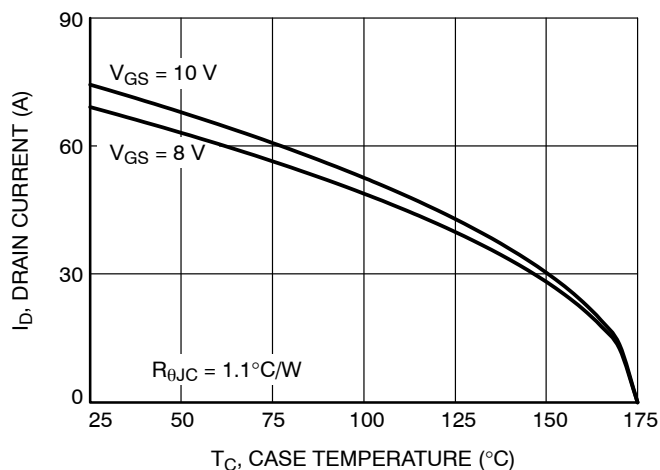


Figure 9. Drain Current vs. Case Temperature

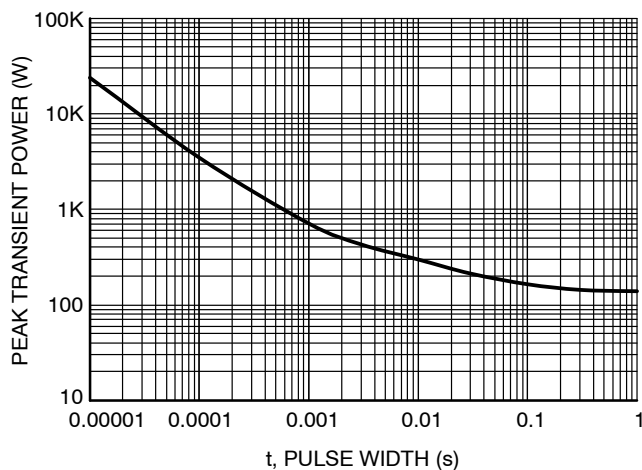


Figure 10. Peak Power

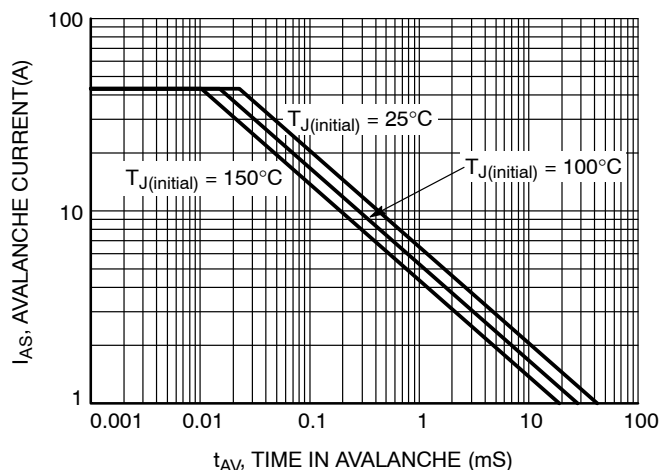


Figure 11. Unclamped Inductive Switching Capability

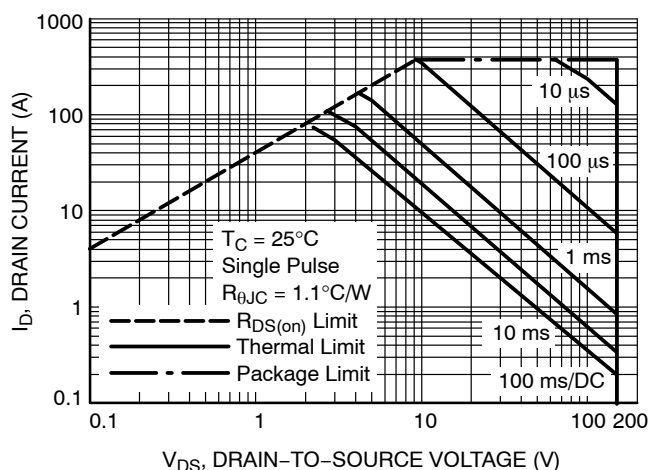


Figure 12. Forward Bias Safe Operating Area

TYPICAL CHARACTERISTICS

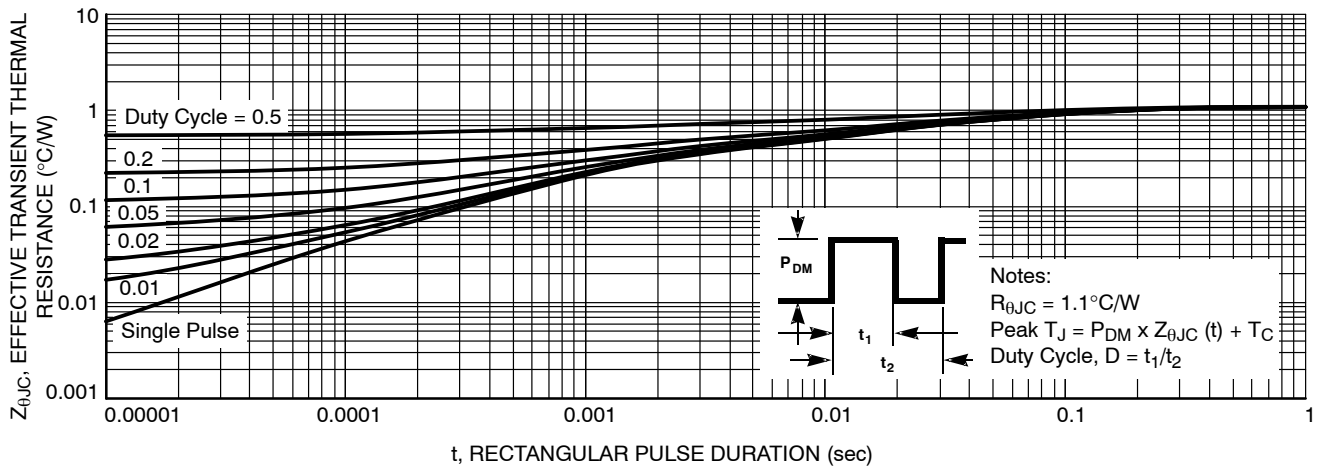
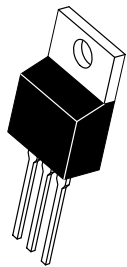
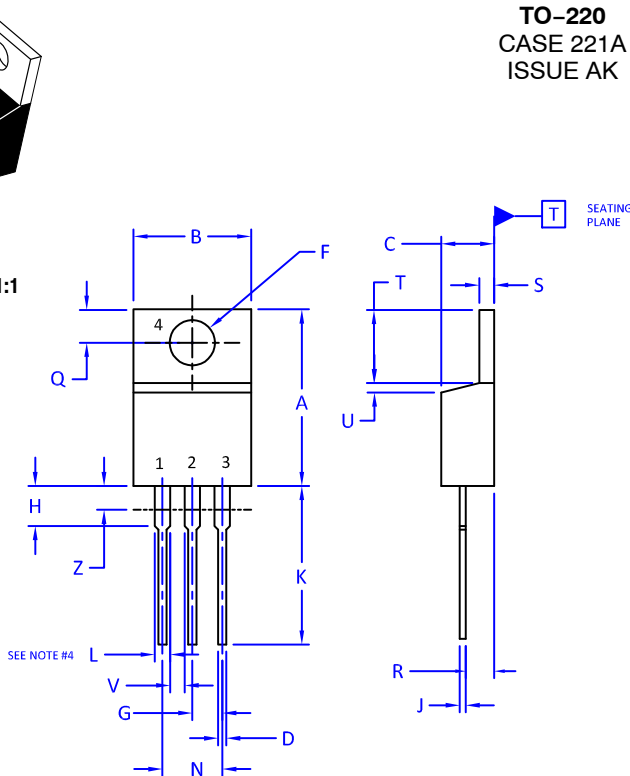


Figure 13. Transient Thermal Impedance



SCALE 1:1



TO-220  
CASE 221A  
ISSUE AK

DATE 13 JAN 2022

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN.   | MAX.  | MIN.        | MAX.  |
| A   | 0.570  | 0.620 | 14.48       | 15.75 |
| B   | 0.380  | 0.415 | 9.66        | 10.53 |
| C   | 0.160  | 0.190 | 4.07        | 4.83  |
| D   | 0.025  | 0.038 | 0.64        | 0.96  |
| F   | 0.142  | 0.161 | 3.60        | 4.09  |
| G   | 0.095  | 0.105 | 2.42        | 2.66  |
| H   | 0.110  | 0.161 | 2.80        | 4.10  |
| J   | 0.014  | 0.024 | 0.36        | 0.61  |
| K   | 0.500  | 0.562 | 12.70       | 14.27 |
| L   | 0.045  | 0.060 | 1.15        | 1.52  |
| N   | 0.190  | 0.210 | 4.83        | 5.33  |
| Q   | 0.100  | 0.120 | 2.54        | 3.04  |
| R   | 0.080  | 0.110 | 2.04        | 2.79  |
| S   | 0.045  | 0.055 | 1.15        | 1.41  |
| T   | 0.235  | 0.255 | 5.97        | 6.47  |
| U   | 0.000  | 0.050 | 0.00        | 1.27  |
| V   | 0.045  | ----  | 1.15        | ---   |
| Z   | ----   | 0.080 | ---         | 2.04  |

STYLE 1:

- PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 2:

- PIN 1. BASE  
2. EMITTER  
3. COLLECTOR  
4. EMITTER

STYLE 3:

- PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

STYLE 4:

- PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. MAIN TERMINAL 2

STYLE 5:

- PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

STYLE 6:

- PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

STYLE 7:

- PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. ANODE

STYLE 8:

- PIN 1. CATHODE  
2. ANODE  
3. EXTERNAL TRIP/DELAY  
4. ANODE

STYLE 9:

- PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 10:

- PIN 1. GATE  
2. SOURCE  
3. DRAIN  
4. SOURCE

STYLE 11:

- PIN 1. DRAIN  
2. SOURCE  
3. GATE  
4. SOURCE

STYLE 12:

- PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. NOT CONNECTED

|                  |             |                                                                                                                                                                                     |
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